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Description

Semiconductor circuit arrangement with trench isolation
5 and fabrication method

The invention relates to a semiconductor circuit arrangement having a substrate, which carries in the order specified:

- 10 - a doped semiconductor layer of a first conductivity type or conduction type,
- an electrically insulating layer,
- and an electrically conductive or an electrically insulating charge-storing layer, which is suitable
15 for the storage of charges.

Moreover, the semiconductor circuit arrangement contains at least one trench which penetrates through the charge-storing layer and also extends into the
20 doped semiconductor layer.

The substrate is for example a wafer made of a semiconductor material, e.g. made of silicon. The layer suitable for the storage of charges is also referred to
25 as floating gate particularly in the case of circuit arrangements having memory cells.

It is an object of the invention to specify an integrated circuit arrangement which is simple to
30 fabricate and simple to drive and, in particular, has very good electrical properties. In particular, the intention is to specify a circuit arrangement having a multiplicity of memory cells. Moreover, the invention relates to a method which can be used, in particular,
35 to fabricate the semiconductor circuit arrangement.

The object related to the circuit arrangement is achieved by means of a circuit arrangement having the

features of patent claim 1. Developments are specified in the subclaims.

5 The invention is based on the consideration that there are in principle two possibilities for fabricating the trench. Thus, it is possible to fabricate the trench, apart from auxiliary layers which are completely removed again after the formation of the trench, before the application of layers which remain in the circuit
10 arrangement, so that the trench does not penetrate through these layers. On the other hand, it is possible to introduce the trench only after layers which remain in the circuit arrangement have been applied to the substrate, so that the trench penetrates through these
15 layers.

The invention is furthermore based on the consideration that the production of the trench after the application of layers which remain in the circuit arrangement
20 simultaneously permits the patterning of these layers and the orientation of the trench with respect to the patterned regions, i.e. a so-called self-alignment. However, it is possible for the trench to be assigned further functions in the integrated circuit
25 arrangement. In the circuit arrangement according to the invention, the trench also serves, moreover, for subdividing the doped semiconductor layer. This requires the trench to be deeper than the thickness of the doped semiconductor layer. Thus, in the circuit
30 arrangement according to the invention, the trench also has, besides the insulating function for insulating adjacent components, two further functions, namely:

- the patterning of the charge-storing layer, and
- the patterning and insulation of the doped
35 semiconductor layer.

In one refinement, the circuit arrangement contains a plurality of trenches arranged next to one another, for example trenches lying parallel to one another.

Arranged between the trenches are in each case a multiplicity of memory cells, in particular EEPROM memory cells or flash EEPROM memory cells (Electrically Erasable Programmable Read Only Memory). In a next
5 refinement, the charge-storing layer is subdivided into charge-storing regions transversely with respect to the direction in which the trenches lie.

In one development of the circuit arrangement, a doped
10 semiconductor layer having a conductivity type opposite to the first conductivity type is arranged between the doped semiconductor layer and the substrate. The trench also penetrates through the semiconductor layer of opposite conduction type and extends into the
15 substrate. The subdivision of a doped semiconductor layer by means of two trenches, e.g. in the so-called bit line direction, already leads to a multiplicity of advantages with regard to the operation of the memory cells. By way of example, memory cells can be
20 selectively erased. The demarcation of a further lower semiconductor layer lying below the upper semiconductor layer with the aid of the trenches leads to a further improvement of the electrical properties. By way of example, there is a reduction in the junction
25 capacitance between the two semiconductor layers for each individual bit line. Furthermore, additional options are afforded for the electrical driving of the components.

30 In an alternative development with two additional semiconductor layers, the trench ends, by contrast, in the semiconductor layer of opposite conduction type, so that only the semiconductor layer of the first conduction type is separated by the trenches. This
35 measure is sufficient for many applications and simpler to carry out than severing both or more than two semiconductor layers with the aid of the trenches.

In one refinement, the substrate is a semiconductor substrate which preferably contains silicon or comprises silicon. The silicon is weakly predoped, for example. In another refinement, the doped semiconductor layer forms the channel region of a transistor or the channel regions of a multiplicity of transistors. In a next refinement, the first conductivity type is the p conductivity type, i.e. electrical conduction through defect electrons or so-called holes. In an alternative refinement, the first conductivity type is the n conductivity type, i.e. electrical conduction through conduction electrons.

In a next refinement, the electrically insulating layer contains an oxide or comprises an oxide, in particular a silicon dioxide which is preferably thermally produced or deposited. During the programming and erasure of the memory cells, charge carriers tunnel through or surmount the electrically insulating layer adjoining the substrate. During programming, e.g. electrons or electron holes are stored in the charge-storing layer. Charge carriers, which are also referred to as hot carriers in this context, are accelerated during programming and/or erasure on account of an electric field in such a way that they can surmount an energy barrier between the charge-storing layer and the substrate. As an alternative, by the application of a suitable potential gradient, the energy barrier may be reduced in such a way that charge carriers can tunnel through it.

In a next refinement, the charge-storing layer contains polycrystalline silicon or comprises polycrystalline silicon, preferably doped polycrystalline silicon. In an alternative refinement, the charge-storing layer contains a nonmetal nitride or comprises a nonmetal nitride, in particular silicon nitride. In another alternative refinement, the charge-storing layer contains another material which is able to bind charge

carriers for example in material defects such as, for example, aluminum oxide or hafnium oxide.

In one development of the circuit arrangement according to the invention, an electrically conductive layer is provided, which is patterned as word lines. A further electrically insulating layer is arranged between the electrically conductive layer and the charge-storing layer. In one refinement, the trench or the trenches which extend into the semiconductor layer do not penetrate through said electrically conductive layer and said electrically insulating layer.

In one refinement, the electrically conductive layer contains a polycrystalline material or a metal. By way of example, the electrically conductive layer comprises polycrystalline silicon, in particular doped polycrystalline silicon. In a next refinement, the electrically conductive layer is subdivided into strips lying transversely or at an angle of 90 degrees with respect to the trenches. In another refinement, the electrically conductive layer has subdivisions at locations at which the charge-storing layer is also subdivided, that is to say that the two layers have been patterned using the same mask.

In one development of the circuit arrangement, there is at least one trench, which is shallower and wider in comparison with the trench penetrating through the electrically insulating layer and which is arranged in the semiconductor layer of the first conductivity type and through which penetrates the deep trench penetrating through the electrically insulating layer. This measure, without relatively high process-technological outlay, results in degrees of freedom for the method implementation, because the shallow trench can be used as additional insulation. The process-technological additional outlay is low because shallow trenches have to be produced anyway in many circuit

arrangements. In particular, shallow trenches are used in logic circuits. Shallow trenches typically have a depth of less than 500 nm (nanometers). By contrast, the deep trench has a depth of greater than 700 nm, greater than 1 μm (micrometer) or even greater than 1.5 μm . The depth of the deep trench depends, in particular, on the voltage conditions, because the latter in turn determine the thickness of the doped semiconductor layers which are intended to be subdivided by the deep trenches parallel to the bit lines.

In a next development of the circuit arrangement, the shallow trench does not penetrate through the charge-storing layer and/or the electrically insulating layer. Thus, the shallow trench must have been fabricated, and in particular also filled, before the application of these two layers. This means that shallow trench and deep trench are processed independently of one another. In particular, the depths of the different types of trench can be defined and optimized independently of one another. Furthermore, this method procedure avoids problems which arise on account of the major height differences in the case of the simultaneous filling of shallow trenches and deep trenches in the case of the subsequent leveling of the surface.

In one development, the shallow trench is completely filled with an electrically insulating material or the shallow trench contains an electrically insulating material, for example silicon dioxide. In a next development, the shallow trench projects symmetrically beyond the deep trench, so that the insulation properties are equally good in a plurality of directions.

In a next development, there is at least one further shallow trench through which no trench, in particular no deep trench, penetrates. In a next development, the

shallow trench through which the deep trench penetrates lies in a memory cell array and the shallow trench through which a trench does not penetrate lies in a logic circuit arrangement in which, by way of example, basic logic functions are produced, e.g. NAND switching functions. The logic circuit is e.g. part of a monolithic circuit which also contains a memory cell array having deep trenches.

10 In a next development, the electrically conductive layer through which the deep trench does not penetrate and/or the electrically insulating layer through which the deep trench does not penetrate are at least partly arranged in the shallow trench. This measure makes it possible to introduce a cutout into the electrically conductive layer through which the deep trench does not penetrate, without stringent requirements being made of its depth. All that is important is that the electrically conductive layer is completely interrupted. There is a relatively large leeway, for example of more than 10 nm or more than 20 nm, for the projection of the cutout into the shallow trench. Despite different depths, it is ensured that the coupling factor between the capacitance of the charge-storing layer and the electrically conductive layer is relatively independent of the depth if the cutout lies within the trench edges of the shallow trench.

In a next development of the circuit arrangement, the circuit arrangement contains a further charge-storing layer, which adjoins the charge-storing layer and, in one refinement, comprises the same material. At least one cutout is arranged in the further charge-storing layer, the bottom of said cutout preferably lying completely within the edge of the deep trench or of the shallow trench. The depth of said cutout is also noncritical provided that the further charge-storing layer is completely patterned. The same relationships

as explained in the previous paragraph hold true with regard to the coupling factor of the capacitances.

5 In another development, the trench is filled with an electrically insulating material or the trench contains an electrically insulating material. In particular, oxides such as silicon dioxide, for example, are suitable for filling the trench. In a next development, the trench contains an electrically conductive or
10 electrically semiconducting material insulated from the trench wall, for example a polycrystalline material, in particular polycrystalline silicon, which is doped or undoped.

15 The invention relates, moreover, to a method for fabricating a semiconductor circuit arrangement, in particular for fabricating the circuit arrangement according to the invention or one of its developments. Thus, the technical effects mentioned above also hold
20 true for the method.

In one development of the method according to the invention, a hard mask layer is used for introducing the deep trench. The hard mask layer can be removed
25 before the trench is filled. However, the hard mask layer can also be removed only after the trench has been filled with a filling material and the filling material has subsequently been etched back. What is achieved by this measure is that, during the etching-
30 back, layers lying below the hard mask are protected by the hard mask.

Exemplary embodiments of the invention are explained below with reference to the accompanying drawings, in
35 which:

Figures 1A to 1F

show fabrication stages in accordance with a first method variant with a hard mask layer

which is removed directly after the fabrication of deep trenches,

Figure 2 shows a fabrication stage in accordance with a second method variant with a hard mask layer which is utilized over a plurality of method steps,

Figures 3A and 3B

show fabrication stages in accordance with a third method variant with shallow trenches through which deep trenches penetrate, and

Figures 4A and 4B

show fabrication stages in accordance with a further method variant with a floating gate double layer.

Figure 1A shows a weakly p-doped semiconductor substrate 10 made of silicon. An n-doped semiconductor layer has been introduced into the semiconductor substrate 10 by doping, said layer lying for example at a depth of 800 nm to 1.6 μm (micrometers). Moreover, a p-doped semiconductor layer 14 has been produced in the semiconductor substrate 10, said layer extending from the surface of the semiconductor substrate down to a depth of about 800 nm. At the edges of a cell array, the semiconductor layers 12 and 14 may be formed as a well, that is to say that they are taken as far as the surface of the semiconductor substrate 10. However, other contact-making possibilities, too, are utilized in another exemplary embodiment.

By way of example, the dopings of the semiconductor layers 12 and 14 are fabricated by implantation. Semiconductor layers 12 and 14 formed in well-type fashion are also referred to as n-well or as p-well.

An oxide layer 16 is subsequently applied, for example thermally, said layer having a thickness of 6 to 15 nm, for example. A floating gate layer 18 is then deposited on the oxide layer 16, said floating gate layer

comprising in-situ-doped polycrystalline silicon, and having a thickness of 50 to 150 nm, for example.

In a subsequent method step, a hard mask layer 20, for example a TEOS layer (Tetra Ethyl Ortho Silicate) having a thickness of hundreds of nm, is applied on the floating gate layer 18. The thickness depends on the selectivity of the trench etching. In other words, given a highly selective etching or another hard mask material, the thickness may also be thinner, under certain circumstances.

As illustrated in Figure 1B, firstly the hard mask layer 20 is patterned with the aid of a lithography method and a photomask (not illustrated), a cutout 30 arising firstly only in the hard mask layer 20. During the fabrication of the cutout 30, etching is effected for example in a time-controlled manner. The photoresist is removed after the patterning of the hard mask layer 20. Afterward, with the aid of the patterned hard mask layer 20, the cutout 30 is extended to form a trench 32 having a depth of about 1.8 μm , for example, measured from the boundary between hard mask layer 20 and floating gate layer 18. By way of example, a reactive ion etching RIE is carried out for the etching of the trench 32. The trench 32 has a width of 200 nm, for example. The hard mask layer 20 is already thinned to a great extent during the etching of the trench 32, so that only an etching reserve of 100 nm, for example, remains.

As illustrated in Figure 1C, the hard mask layer 20 is subsequently removed or etched away. Afterward, a so-called liner oxidation is carried out, during which an oxide layer 40 having a thickness of 40 nm, for example, is produced at the wall of the trench 32 and on the floating gate layer 18. After the production of the liner oxide layer 40, a polycrystalline silicon layer 42 is deposited, which completely fills the

trench 32. By way of example, a low-pressure CVD method (Chemical Vapor Deposition) is utilized for the deposition of the silicon layer 42. In the exemplary embodiment, the polycrystalline silicon layer 42 is undoped. In another exemplary embodiment, however, a doped polycrystalline silicon layer 42 is fabricated.

As illustrated in Figure 1D, regions of the silicon layer 42 which lie outside the trench 32 are subsequently removed, for example with the aid of a reactive ion etching method. Moreover, in the upper region of the trench 32, the silicon layer 42 is removed selectively with regard to the oxide layer 40, for example down to a depth of 300 nm below the boundary between oxide layer 16 and p-doped semiconductor layer 14. After the etching of the silicon layer 42, an insulating filling material 50 is introduced into the upper part of the trench 32, for example silicon dioxide with the aid of an HDP method (High Density Plasma). An oxide layer 50 is produced in the upper region of the trench 32 and on the floating gate layer 18.

As illustrated in Figure 1E, the oxide layer 50 is subsequently etched back over the whole area, a cutout 60 arising in the upper region of the trench 32. The etching-back of the oxide layer 50 is carried out for example with the aid of an RIE method (reactive ion etching) or with the aid of a wet etching. The bottom of the cutout 60 should not lie below the boundary between oxide layer 16 and p-doped semiconductor layer 14.

As shown in Figure 1F, a dielectric layer 70 is subsequently deposited, for example an ONO layer (Oxide-Nitride-Oxide). The dielectric layer 70 has a thickness of less than 20 nm, for example. After the application of the dielectric layer 70, a control gate layer 72 is applied, for example made of in-situ-doped

polycrystalline silicon and having a thickness of e.g. greater than 100 nm.

In subsequent method steps (not illustrated), the
5 control gate layer 72, the dielectric layer 70 and the
floating gate layer 18 are patterned simultaneously in
a word line direction, which lies parallel to the sheet
plane, see arrow 74. A bit line direction lies
10 perpendicular to the sheet plane and corresponds to the
direction of the trench 32. After the patterning of the
control gate layer 72, channel and source regions are
introduced into the p-doped semiconductor layer 14 by
doping, said regions lying in front of and behind the
sheet plane, respectively, with reference to Figure 1F.
15 One or a plurality of metallization layers for making
contact with the memory cells are applied in further
method steps. Finally, a memory circuit 76 is
completed, containing the arrangement illustrated in
Figure 1F.

20
Figure 2 shows a fabrication stage in accordance with a
second method, in which a hard mask layer 20a is used
over a plurality of method steps. Proceeding from a
semiconductor substrate 10a, the method steps presented
25 above with reference to Figures 1A and 1B are performed
for producing an n-doped semiconductor layer 12a, a
p-doped semiconductor layer 14a, an oxide layer 16a and
a floating gate layer 18a. Reference is made to Figures
1A to 1B with regard to the details. Afterward, the
30 hard mask layer 20a is applied and patterned with the
aid of a photolithographic method, the floating gate
layer 18a initially remaining unpatterned. After the
removal of the photoresist, the patterned hard mask
layer 20a is used for producing a trench 32a having the
35 same properties as the trench 32.

With the hard mask layer 20a still present on the oxide
layer 18a, a for example thermal liner oxidation is
subsequently carried out for producing an oxide layer

40a situated at the walls of the trench 32a and on the hard mask layer 20a.

In a next method step, a doped or undoped polycrystalline silicon layer 42a is deposited, which completely fills the trench 32a. Afterward, the polycrystalline silicon layer 42a is etched back for example with the aid of a reactive ion etching method, the silicon layer 42a being removed outside the trench 32a and in the upper region thereof. Those regions of the oxide layer 40a which lie on the hard mask layer 20a are also removed in this case. The hard mask layer 20a protects the floating gate layer 18a during the etching-back.

The hard mask layer 20a is removed after the etching-back. Afterward, further processing is effected in the manner explained above with reference to Figures 1D to 1F, i.e. application of an oxide layer corresponding to the oxide layer 50, etc.

Figures 3A and 3B show fabrication stages in accordance with a third method variant, in which a deep trench 32b penetrates through a shallow trench 100. The shallow trench 100 is produced in a semiconductor substrate 10b, corresponding to the semiconductor substrate 10, before or after the application of an oxide layer 16b, corresponding to the oxide layer 16, and a floating gate layer 18b, corresponding to the floating gate layer 18, for example before the implantation for producing an n-doped semiconductor layer 12b or a p-doped semiconductor layer 14b. Except for the introduction of the trench 100, the method steps explained with reference to Figures 1A to 1D are performed unchanged, see broken line 100 in said figures. When the state illustrated in Figure 1D is reached, an oxide layer corresponding to the oxide layer 50 is etched back, a cutout 60b arising in the upper region of the trench 32b. During the etching-

back, it is not critical if the bottom of the cutout 60b lies below the boundary between the oxide layer 16b and the semiconductor layer 14b. By way of example, it is possible to etch into the shallow trench 100 to an extent of tens of nm, see broken line 102. The trench 100 is filled with an insulating material, for example with silicon dioxide. This insulating material, even with the bottom of the cutout 60b lying at a deeper level, affords a sufficient insulation between the subsequently applied control gate and the semiconductor layer 14b.

This is because the trench 100 has a larger width than the trench 32b. In the exemplary embodiment, the shallow trench 100 has a width of 300 nm and a depth of 400 nm. Given a symmetrical arrangement of the deep trench 32b with respect to the shallow trench 100, the shallow trench 100 projects beyond the deep trench 32b by a distance A of 50 nm on each side. The larger width of the trench 100 also prevents instances of incipient etching of the tunnel oxide 16b in edge regions of the trench 100 during the etching of the cutout 60b, see regions 104 and 106, which leads to a higher reliability.

As illustrated in Figure 3B, a dielectric layer 70b, corresponding to the dielectric layer 70, is subsequently applied. A control gate layer 72b, corresponding to the control gate layer 72, is then applied. The other method steps explained with reference to Figure 1F are subsequently performed.

The method with a shallow trench through which a deep trench penetrates is carried out, in accordance with a fourth method variant, also in the case of the method variant explained with reference to Figure 2, see broken line 100 in Figure 2. That is to say that a hard mask layer corresponding to the hard mask layer 20a can be utilized for a plurality of method steps even when a

deep trench corresponding to the deep trench 32a penetrates through the shallow trench 100.

Figures 4A to 4B show a fifth method variant, in which
5 a floating gate double layer comprising a floating gate layer 18c, corresponding to the floating gate layer 18, and a floating gate layer 110 is fabricated. The method steps up to the etching-back of an oxide layer 50c corresponding to the oxide layer 50 are the same as
10 explained above with reference to Figures 1A to 1D. For a semiconductor substrate 10c, an n-doped semiconductor layer 12c, a p-doped semiconductor layer 14c, an oxide layer 16c, a trench 32c, an oxide layer 40c and a polycrystalline silicon trench filling 42c, reference
15 is made to the explanations with respect to Figures 1A to 1D.

In a departure from the method explained with reference to Figure 1D, the oxide layer 50c is etched back only
20 as far as the floating gate layer 18c, the floating gate layer 18c serving as an etching stop layer. The trench 32c thus remains filled with the oxide layer 50c in its upper region as well.

25 This procedure, as also explained with reference to Figure 3A, prevents damage to the thin oxide of the oxide layer 16c at the edges 112 and 114 of the trench 32c during the etching-back of the oxide layer.

30 The floating gate layer 110 is then deposited, for example polycrystalline silicon, which is doped in situ.

As illustrated in Figure 4B, the floating gate layer
35 110 is then patterned with the aid of a photolithographic method. In this case, a cutout 120 is produced above the trench 32c, the width of said cutout being less than the width of the trench 32c. The cutout 120 is oriented symmetrically with respect to the

trench center of the trench 32c. During the etching of the cutout 120, care has to be taken only to ensure that the floating gate layer 110 is completely severed. An overetching is not critical, because the bottom of the cutout 120 is surrounded on all sides by that part of the oxide layer 50c which remains in the trench 32c, see broken line 122. Even when the bottom of the cutout 120 is in a different position, there is only an insignificant change in a coupling factor of the capacitances between the floating gate and the control gate of the memory cells to be fabricated on account of the projection of the floating gate layer 110 over the floating gate layer 18c.

Afterward, the method steps explained above with reference to Figure 1F are carried out. Instead of a three-layer ONO layer, it is also possible to use a single-layer dielectric layer.

In accordance with a sixth method variant, the methods in accordance with Figure 2 and in accordance with Figures 4A and 4B are combined, so that the hard mask is utilized for a plurality of method steps even in a method in which a floating gate double layer is produced. The etching-back of the oxide layer is then carried out e.g. in a time-controlled manner. The hard mask is then removed.

The cutout 120 can also be made wider than the trench 32c. On the basis of the two lithography methods for the two floating gate layers 18c and 110, the width of the trench 32c and the width of the cutout 120 can be chosen independently of one another.

In other exemplary embodiments, a CMP method (Chemical Mechanical Polishing) is also used instead of etching-back. Instead of a hard mask layer made of TEOS, it is also possible to use a hard mask layer made of another material, for example made of a nitride such as silicon

nitride. If the deep trench has a smaller depth than in the exemplary embodiments, a photoresist layer may also be used instead of the hard mask.

- 5 Consequently, a plurality of variants for fabricating nonvolatile memory cells has been explained, in which:
- deep isolation trenches are used for flash EEPROM memory cells or for simple EEPROM memory cells,
 - method sections, i.e. so-called modules, for
- 10 fabricating shallow isolation trenches (STI - Shallow Trench Isolation) and modules for fabricating and filling deep trenches (DTI - Deep Trench Isolation) can be carried out in a simple manner, in particular successively, in a fabrication process, and
- 15 - the problems of "classic" integration, in which deep trenches and shallow trenches are fabricated at the start of the method, are avoided. In particular, no problems arise during the planarization of HDP oxide fillings (High Density Plasma) which have a different
- 20 height above the shallow trenches and the deep trenches.

In the exemplary embodiments explained, deep trench isolations lead to insulated well strips. The trenches

25 in the memory cell array have a larger depth than trenches in the drive circuit of the memory array or in a logic circuit applied on the same chip. On account of the filling with polycrystalline silicon, it is possible to fabricate deep trenches having a small

30 ratio of width to depth, e.g. with ratios smaller than 1/4 or 1/10.

The methods explained are suitable in particular for memory cells based on a cell concept in which the

35 charges are applied to the floating gate or are removed from the floating gate on the basis of the Fowler-Nordheim tunnel effect.

The variant with a deep trench through which no shallow trench penetrates makes it possible:

- to manage with a small chip area for the insulation,
- to avoid problems of alignment between shallow
5 trenches and deep trenches, so that no additional tolerances have to be provided, and
- to planarize shallow trenches lying outside the cell array without any problems.

10 The variant with a deep trench through which a shallow trench penetrates makes it possible:

- to improve the insulation between control gate and substrate or p-doped region,
- to achieve larger coupling factors on account of the
15 reduced coupling of floating gate and substrate,
- to be able to set the coupling factor better, and
- to be able to etch back the filling oxide of the trench more easily.

20 Both variants make it possible:

- to avoid additional CMP steps (Chemical Mechanical Polishing),
- to avoid a CMP method with major height differences, and
- 25 - to carry out and to optimize processes for fabricating the shallow trenches independently of processes for fabricating the deep trenches.

The methods explained make it possible, in particular,
30 to avoid or reduce damage to the sensitive tunnel oxide in particular at the edges of the trenches, so that the yield and reliability increase. Moreover, it is thus possible to produce strips made from the doped wells in a simple manner, said strips running in the bit line
35 direction.

In other exemplary embodiments, the same structures are fabricated based on other doping layer sequences, e.g. p-substrate and n-well. An alternative is to work with

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n-substrate and p-well. A third alternative works with n-substrate and p-well and also n-well.